

Amendments to the Claims

1. (*Original*) A method of manufacturing an electronic device comprising a carrier having, between a first and an opposite second side, a first patterned metal layer, a patterned intermediate layer, a second patterned metal layer and an etch mask, which first metal layer is electroconductively connected to an electric element and to the second metal layer, and comprises parts projecting with respect to the intermediate layer,

which method comprises the steps of:

placing an electric element on the first side of the carrier, contacts of the electric element being electroconductively connected to the first metal layer;

applying an envelope, the projecting parts of the first metal layer being anchored in the envelope; and

etching the second metal layer from the second side of the carrier in accordance with the pattern defined by the etch mask.

2. (*Original*) A method as claimed in claim 1, characterized in that the etch mask has an adhesive layer for solder, which adhesive layer is also present on the first side of the carrier.

3. (*Original*) A method as claimed in claim 2, characterized in that the first metal layer and the intermediate layer are patterned by:

patterning the first metal layer in accordance with a desired pattern, the adhesive layer present in accordance with the desired pattern being used as an etch mask, and

patterning the intermediate layer by means of an etchant which is selective with respect to the first and the third metal layer, underetching taking place with respect to the first metal layer.

4. (*Original*) A carrier with a first and a second side, comprising a stack of:

a first etch mask,

a first metal layer,

an intermediate layer,

a second metal layer and
a second etch mask,
the first etch mask being situated on the first side of the carrier, and the second etch mask being situated on the second side of the carrier.

5. *(Original)* A carrier as claimed in claim 4, characterized in that the first metal layer and the intermediate layer are patterned such that the first metal layer comprises parts projecting with respect to the intermediate layer.

6. *(Currently Amended)* A carrier as claimed in claim 4, ~~claim 4 or 5~~, characterized in that the first and the second etch mask comprise an adhesive layer for solder.

7. *(Original)* A carrier as claimed in claim 6, characterized in that the adhesive layer for solder comprises a material selected from the group composed of Ag, NiPd, NiPdAu.

8. *(Currently Amended)* A carrier as claimed in claim 4, ~~claim 4 or 5~~, characterized in that the intermediate layer comprises an electroconductive material that can suitably be used as a solder stop.

9. *(Original)* A carrier as claimed in claim 8, characterized in that the intermediate layer comprises a material selected from the group composed of Al, an alloy of Al, FeNi, FeCrNi and stainless steel, and that the first and the third metal layer contain copper.

10. *(Original)* A method of manufacturing a carrier having a first side and a second side opposite thereto, comprising the steps of:

providing a stack of a first metal layer, an intermediate layer and a second metal layer, wherein the first and the second metal layer are electroconductively interconnected, and wherein the intermediate layer comprises a material that can be selectively etched with respect to the first metal layer, and wherein the first metal layer is situated on the first side;

applying and patterning a photosensitive layer on the second side; and

electrochemically providing an adhesive layer for solder on the first and the second side.

11. (*Original*) A method as claimed in claim 10, characterized in that prior to the provision of the adhesive layer, a photosensitive layer is provided on the first side and subsequently patterned.

12. (*Original*) A method as claimed in claim 11, which additionally comprises the steps of:

 patterning the first metal layer in accordance with a desired pattern, in which process the adhesive layer serves as an etch mask, and

 patterning the intermediate layer using an etchant which is selective with respect to the first and the third metal layer, resulting in underetching with respect to the first metal layer.